

MOSFET
Small Signal MOSFET, -60 V

Features

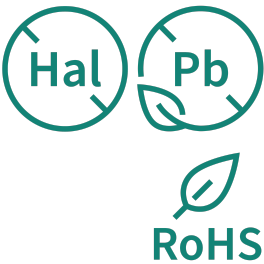
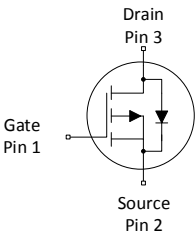
- P-channel
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Logic level

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on),max}$	1700	mΩ
I_D	-0.55	A
Q_{oss}	-0.6	nC
Q_G	-0.87	nC



Part number	Package	Marking	Related links
BSS83I	PG-SOT23-3	YJ	-



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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	-0.55	A	$V_{GS}=-10\text{ V}$, $T_C=25\text{ °C}$
				-0.35		$V_{GS}=-10\text{ V}$, $T_C=100\text{ °C}$
				-0.31		$V_{GS}=-4.5\text{ V}$, $T_C=100\text{ °C}$
				-0.32		$V_{GS}=-10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=350\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	-2.2	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	25	mJ	$I_D=-0.3\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	1.04	W	$T_C=25\text{ °C}$
				0.4		$T_A=25\text{ °C}$, $R_{thJA}=350\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	120	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}			350		

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=-250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-1.5	-2.0	V	$V_{DS}=V_{GS}$, $I_D=-34\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-0.1	-1	μA	$V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$
			-10	-100		$V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	$V_{GS}=-20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1355.7	1700	m Ω	$V_{GS}=-10\text{ V}$, $I_D=-0.3\text{ A}$
			1634.3	2200		$V_{GS}=-4.5\text{ V}$, $I_D=-0.29\text{ A}$
Gate resistance	R_G	-	100	-	Ω	-
Transconductance	g_{fs}	-	0.64	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=-0.3\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance ⁵⁾	C_{iss}	-	55	72	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁵⁾	C_{oss}		9	12		
Reverse transfer capacitance ⁵⁾	C_{rss}		3	5		
Turn-on delay time	$t_{d(on)}$	-	3.5	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-0.3\text{ A}$, $R_{G,ext}=6\text{ }\Omega$
Rise time	t_r		2.6			
Turn-off delay time	$t_{d(off)}$		18.5			
Fall time	t_f		32.3			

⁵⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁶⁾

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	-0.16	-	nC	$V_{DD} = -30\text{ V}$, $I_D = -0.3\text{ A}$, $V_{GS} = 0\text{ to } -4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$		-0.08	-	nC	
Gate to drain charge ⁷⁾	Q_{gd}		-0.45	-0.68	nC	
Switching charge	Q_{sw}		-0.53	-	nC	
Gate charge total ⁷⁾	Q_g		-0.87	-1.09	nC	
Gate plateau voltage	$V_{plateau}$		-3	-	V	
Gate charge total	Q_g	-	-1.79	-2.4	nC	$V_{DD} = -30\text{ V}$, $I_D = -0.3\text{ A}$, $V_{GS} = 0\text{ to } -10\text{ V}$
Output charge ⁷⁾	Q_{oss}	-	-0.6	-0.8	nC	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$

⁶⁾ See "Gate charge waveforms" for parameter definition

⁷⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-0.55	A	$T_C = 25\text{ °C}$
Diode pulse current	$I_{S,pulse}$			-2.2		
Diode forward voltage	V_{SD}	-	-0.83	-1.2	V	$V_{GS} = 0\text{ V}$, $I_F = -0.3\text{ A}$, $T_J = 25\text{ °C}$
Reverse recovery time ⁸⁾	t_{rr}	-	13.4	26.8	ns	$V_R = -30\text{ V}$, $I_F = -0.3\text{ A}$, $di_F/dt = -100\text{ A}$
Reverse recovery charge ⁸⁾	Q_{rr}		8.4	16.8	nC	

⁸⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

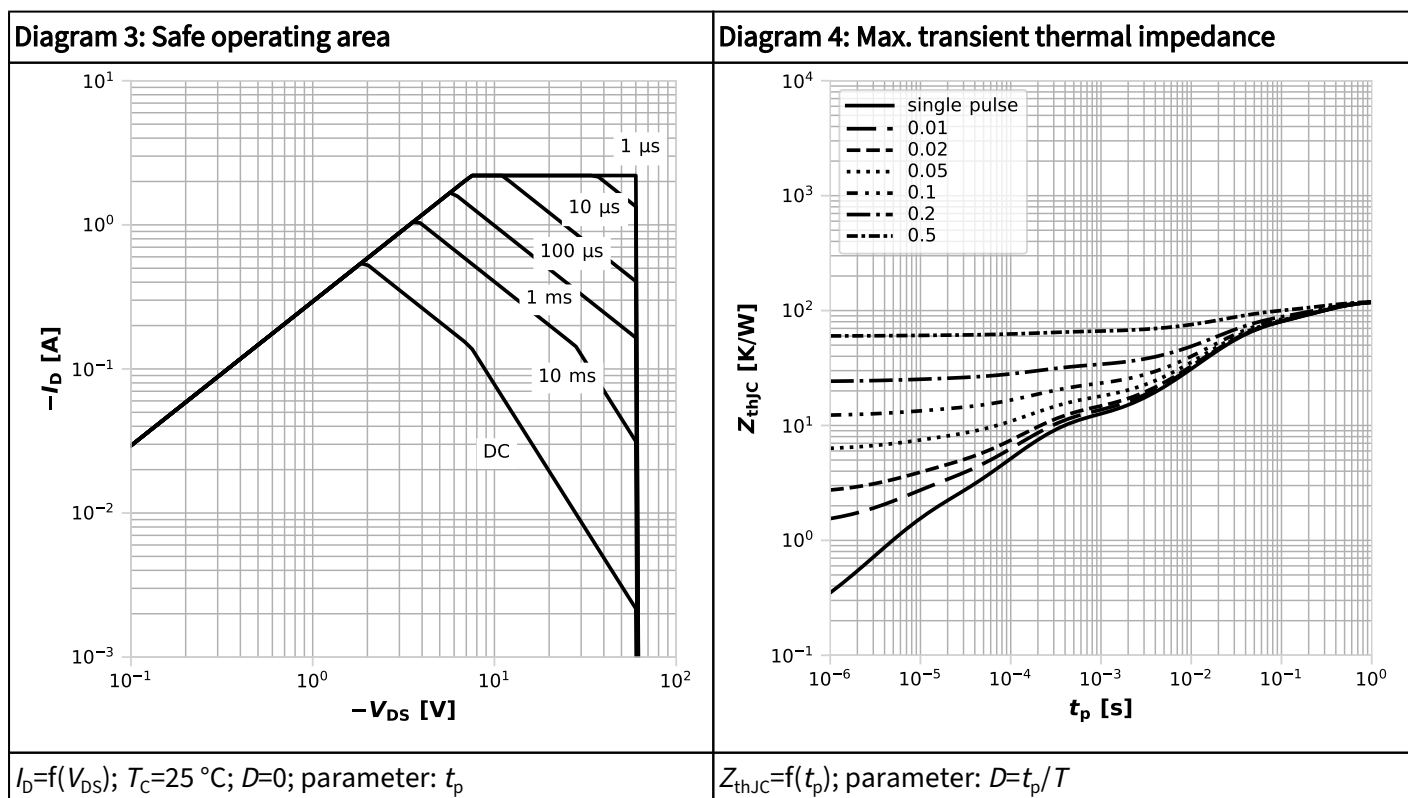
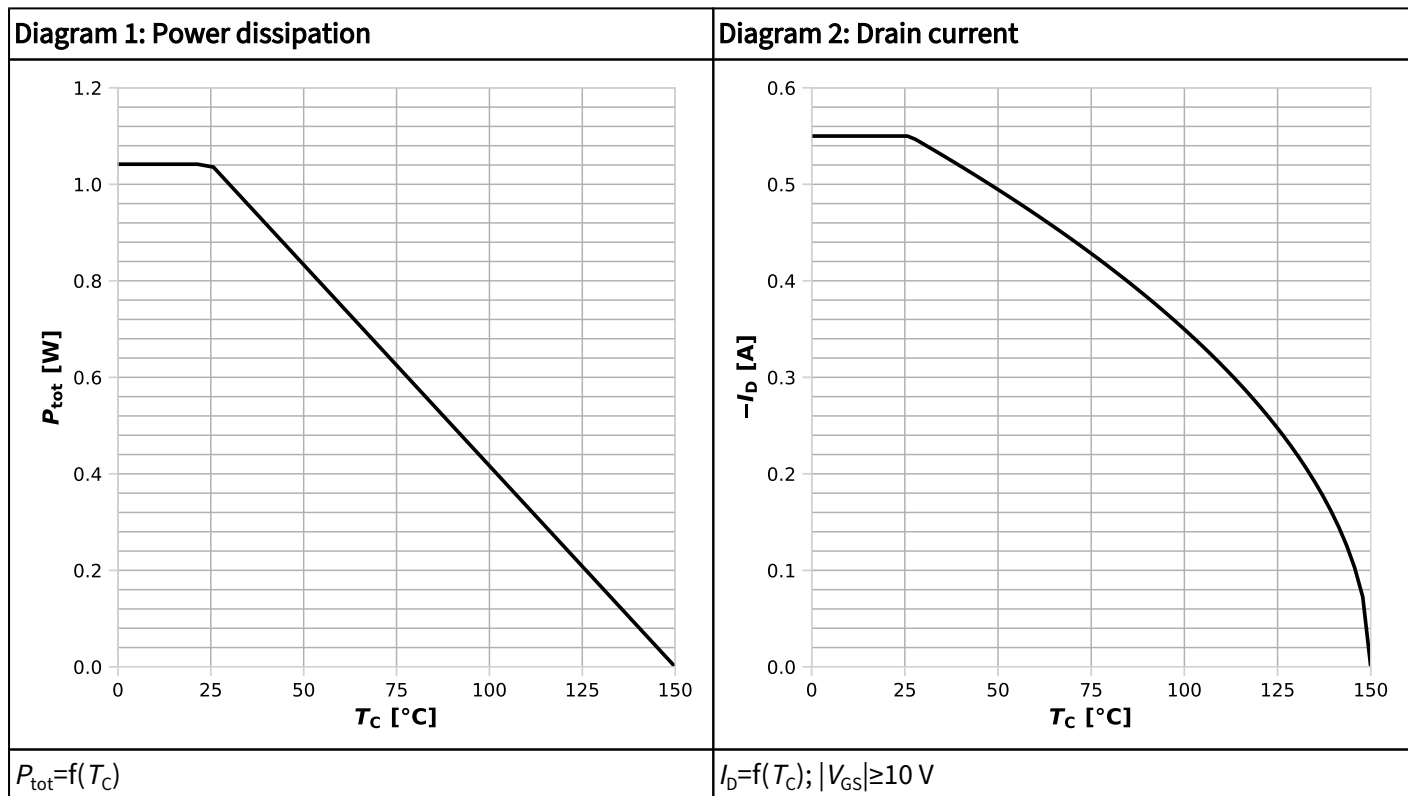
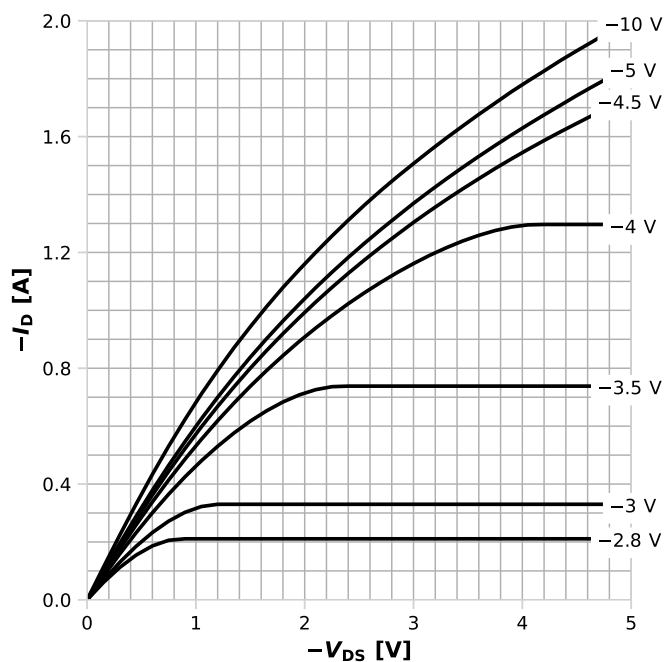
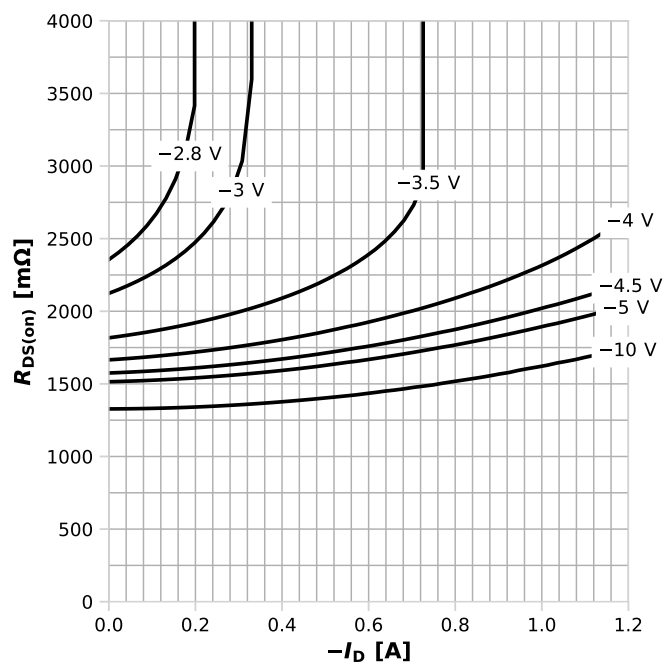


Diagram 5: Typ. output characteristics



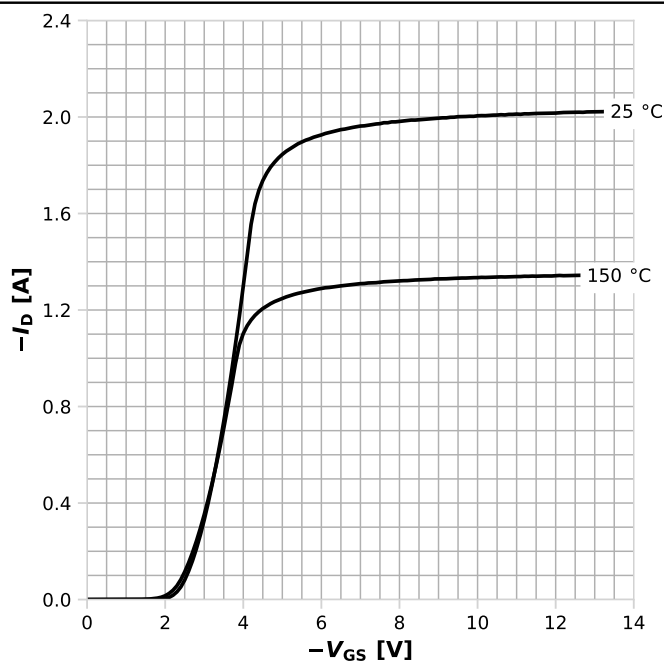
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



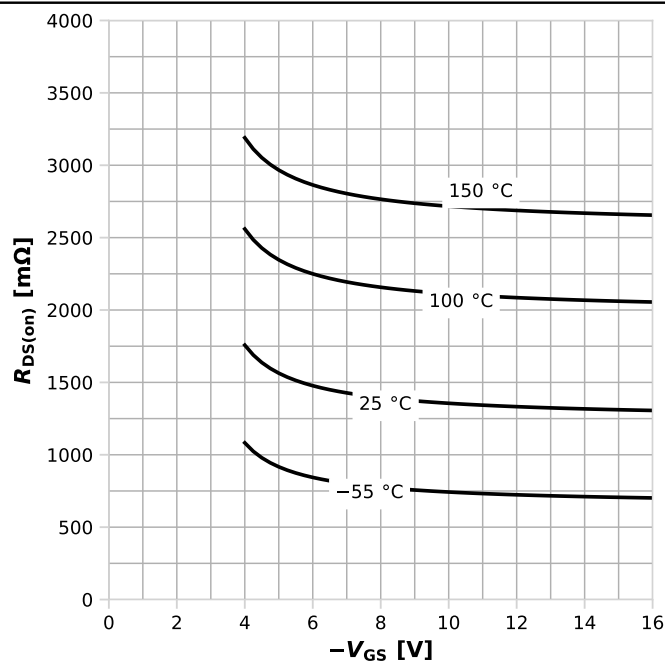
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



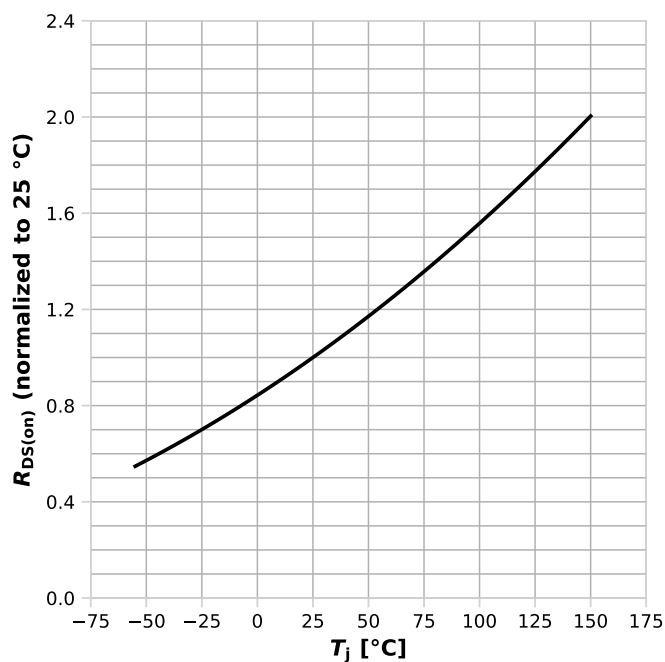
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



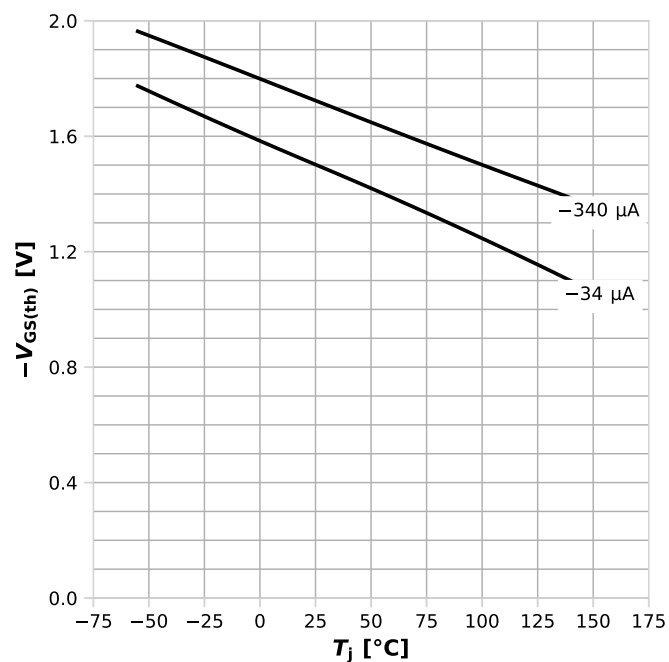
$R_{DS(on)} = f(V_{GS})$, $I_D = -0.3\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



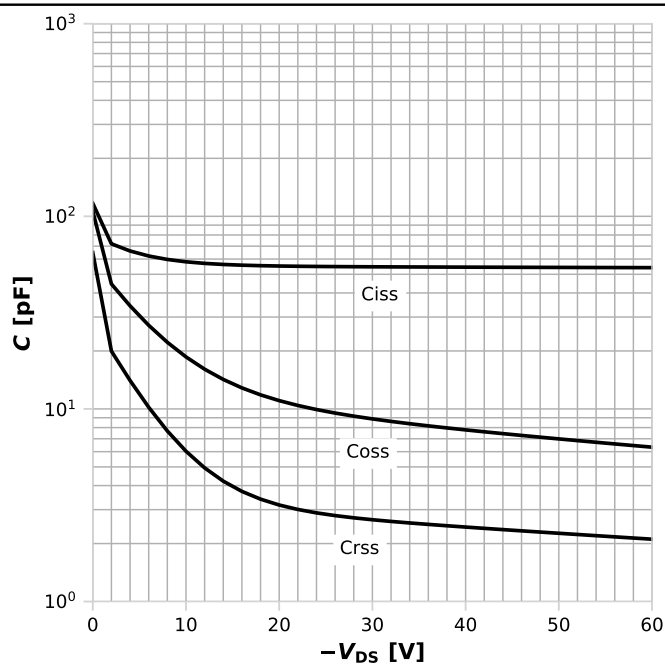
$$R_{DS(on)} = f(T_j), I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



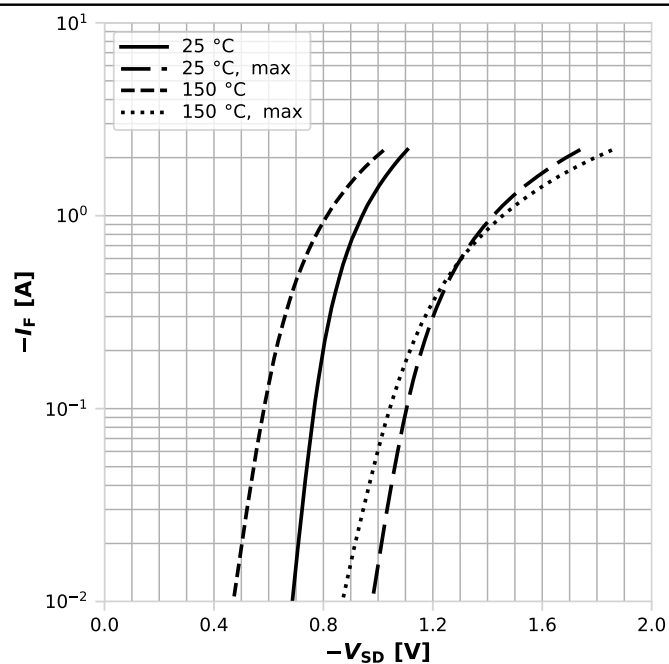
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances



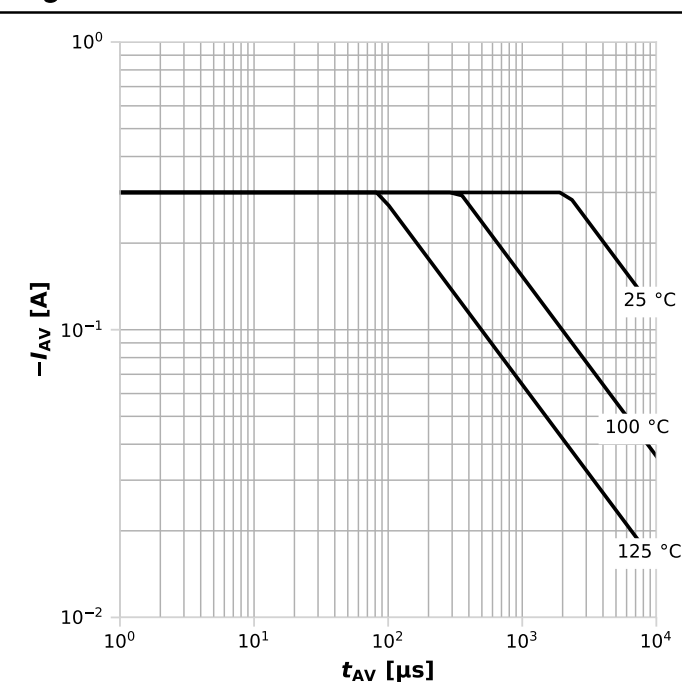
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



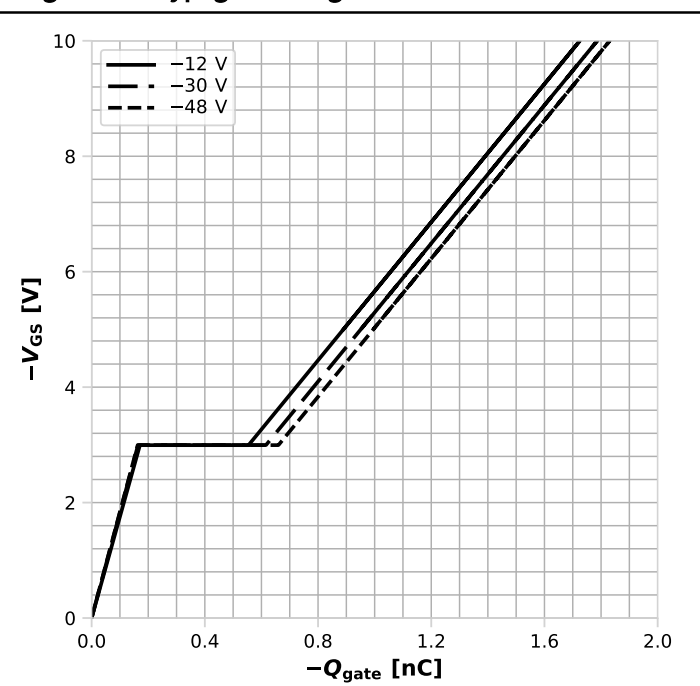
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



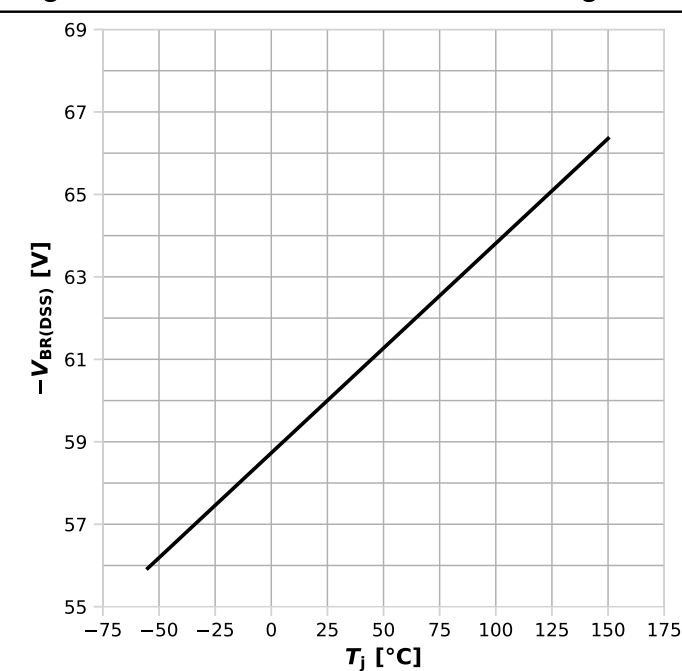
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



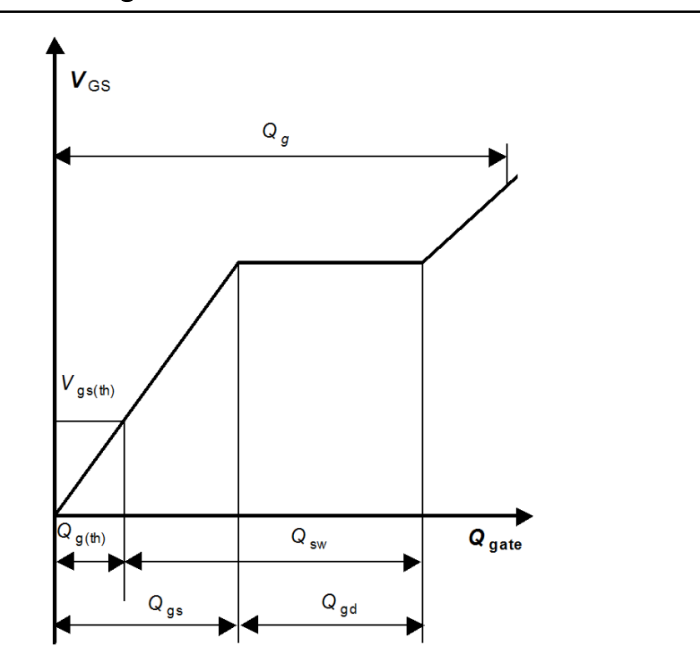
$V_{GS}=f(Q_{gate})$, $I_D=-0.3\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage



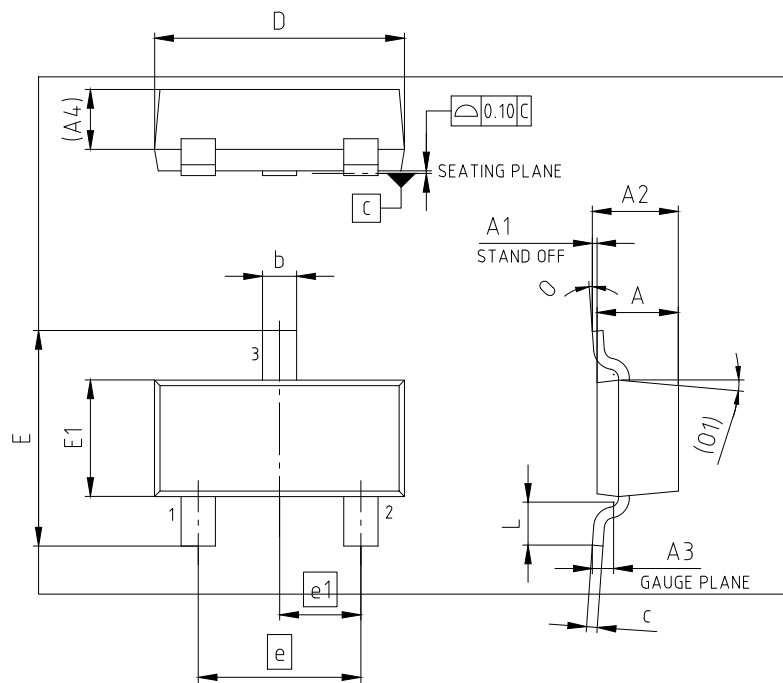
$V_{BR(DSS)}=f(T_j)$; $I_D=-250\ \mu\text{A}$

Gate charge waveforms



-

5 Package outlines



PACKAGE - GROUP NUMBER: PG-SOT23-3-U03					
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	0.88	1.02	e	1.90	
A1	0.01	0.10	e1	0.95	
A2	0.89	1.12	L	0.40	0.60
A3	0.15	0.35	N	3	
A4	0.70		O	3°	8°
b	0.32	0.47	O1	6°	8°
c	0.08	0.18			
D	2.80	3.04			
E	2.40	2.64			
E1	1.32	1.40			

NOTE: ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

Figure 1 Outline PG-SOT23-3mm

Revision history

BSS83I

Revision 2025-02-16, Rev. 2.0

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2025-02-16	Release of final datasheet

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